

Figure 1. Cross-sectional schematic of a vertical GaN PCSS with incident light at the surface

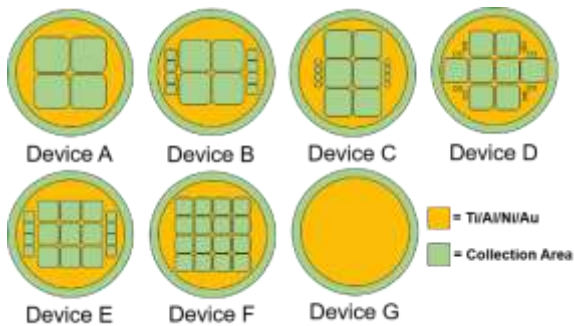


Figure 2. Plan view schematic of different vertical GaN PCSS geometries investigated, showing the additional collection area outside the device. The internal collection area is the same in devices A through F.

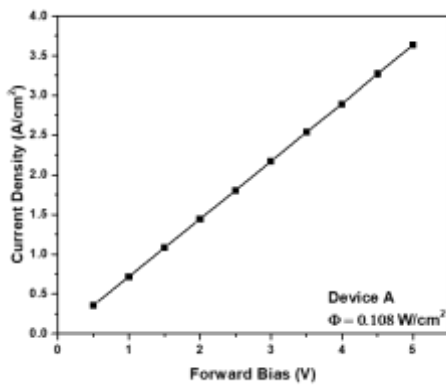


Figure 3. Forward I-V curves showing a forward current normalized to collection area.

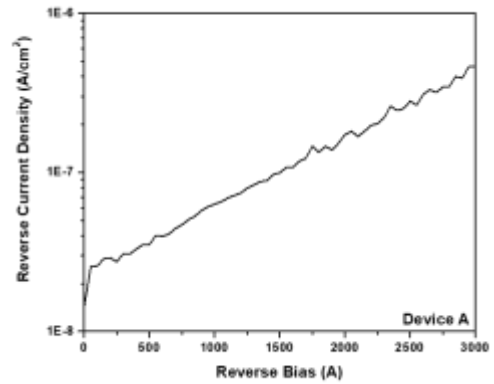


Figure 4. Off-state measurement of vertical PCSS with up to a reverse bias of 3000 V.

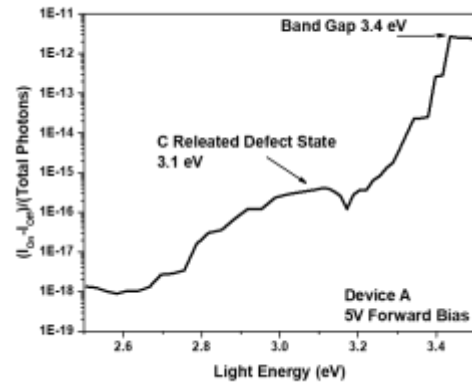


Figure 5. Photoionization spectroscopy under forward of 5 V, showing band gap response at 3.4 eV and an impurity related response at from centered around 3.1 eV.